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**Vishay Semiconductors** 

# Thyristor High Voltage, Phase Control SCR, 50 A



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PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	50 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V				
V <sub>TM</sub> (typ.)	1.1 V				
I <sub>GT</sub> (typ.)	40 mA				
TJ	-40 °C to +150 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

#### **FEATURES**

- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>
  Halogen

#### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### DESCRIPTION

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V			
V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.1	v			
I <sub>T(AV)</sub>		50				
I <sub>RMS</sub>		79	А			
I <sub>TSM</sub>		630				
dV/dt		1000	V/µs			
T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C			

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA
VS-50TPS12L-M3	1200	1300	10



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ABSOLUTE MAXIMUM RATING	ABSOLUTE MAXIMUM RATINGS								
DADAMETER				VAL	UNITS				
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 112 \ ^{\circ}C$ , 180° conduction half sine w	ave	-	50				
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	79	А			
Peak, one-cycle non-repetitive surge current		10 ms sine pulse, rated $V_{RRM}$ applied		-	530				
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630				
I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{\text{RRM}}$ applied	maximum	-	1405	A <sup>2</sup> s			
I-t for fushing	1-1	10 ms sine pulse, no voltage reapplied		-	1986				
I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	, T <sub>J</sub> = 125 °C	-	19 850	A²√s			
Low level value of threshold voltage	V <sub>T(TO)1</sub>			-	0.89	v			
High level value of threshold voltage	V <sub>T(TO)2</sub>	T _ 195 °C		-	0.97	v			
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C			6.77	mΩ			
High level value of on-state slope resistance	r <sub>t2</sub>				6.32				
On-state voltage	VT	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	v			
OII-State Voltage	۷Ţ	100 A, T <sub>J</sub> = 25 °C		1.4	1.6	v			
Rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		-	150	A/µs			
Holding current	Ι <sub>Η</sub>	Anode $aupply = 6 V$ , registive load $T = 2$	E °C	-	300				
Latching current	١L	Anode supply = 6 V, resistive load, $T_J = 2$	5 0	-	350	mA			
Poverse and direct lookage ourrent	1	T <sub>J</sub> = 25 °C		-	0.05	ШA			
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			10				
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V <sub>DRM</sub> , R	$_{g}-k = \infty \Omega$	-	1000	V/µs			

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P <sub>GM</sub>	10 ma aina pula	e, no voltage reapplied	-	10	w
Average gate power	P <sub>G(AV)</sub>	TO THIS SITTLE PUIS	e, no voltage reapplied	-	2.5	vv
Peak gate current	I <sub>GM</sub>			-	2.5	Α
Peak negative gate voltage	-V <sub>GM</sub>			-	10	
		$T_J = -40 \ ^\circ C$		-	1.6	v
Required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	-	1.5	v
		T <sub>J</sub> = 150 °C		-	1	
		T <sub>J</sub> = -40 °C		-	160	
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	45	100	mA
		T <sub>J</sub> = 150 °C		-	60	
DC gate voltage not to trigger	V <sub>GD</sub>	T 150 °C V		-	0.2	V
DC gate current not to trigger	I <sub>GD</sub>	$1_{\rm J} = 150 {}^{\rm 2}{\rm C},  V_{\rm D}$	<sub>RM</sub> = rated value	-	3	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Turn-on time	t <sub>gt</sub>	$I_T$ = 50 A, $V_D$ = 50 % $V_{DRM},~I_{gt}$ = 300 mA, $T_J$ = 25 $^\circ C$	1.5	
Turn-off time	tq	$ I_{T} = 50 \text{ A}, V_{D} = 80 \ \% \ V_{DRM}, \ dV/dt = 20 \ V/\mu s, \ t_{p} = 200 \ \mu s \\ I_{gt} = 100 \ mA, \ dI/dt = 10 \ A/\mu s, \ V_{R} = 100 \ V, \ T_{J} = 150 \ ^{\circ}C $	92	μs

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum junction and storage te	emperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C
Maximum thermal resistance, jur	iction to case	R <sub>thJC</sub>		-	0.35	
Maximum thermal resistance, jur	ction to ambient	R <sub>thJA</sub>		-	40	°C/W
Typical thermal resistance, case	to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.2	-	
Mounting torgue	minimum			6	(5)	kgf · cm
maximum				12 (10)		(lbf · in)
Marking device			Case style Super TO-247AD 3L		50TPS12	L

#### **ARthJ-HS** CONDUCTION PER JUNCTION

DEVICE SINE HALF-WAVE CONDUCTION						RECTANGULAR WAVE CONDUCTION				UNITS	
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

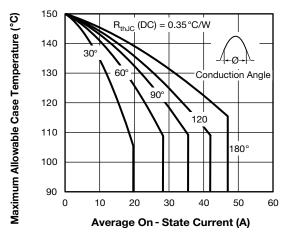


Fig. 1 - Current Rating Characteristics

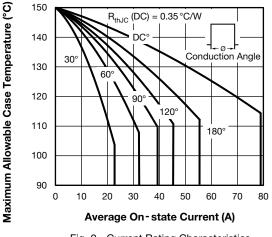


Fig. 2 - Current Rating Characteristics

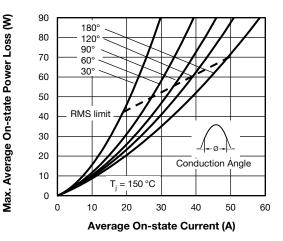


Fig. 3 - On-State Power Loss Characteristics

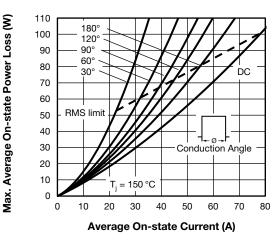


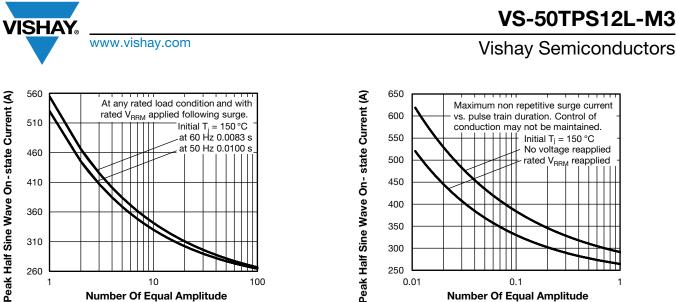
Fig. 4 - On-State Power Loss Characteristics

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Half Cycle Current Pulse (N)

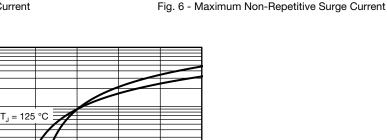
Fig. 5 - Maximum Non-Repetitive Surge Current

1000

100

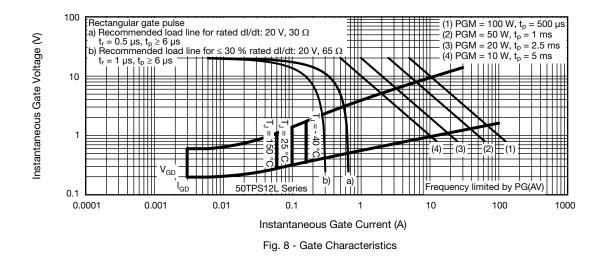
10

Instantaneous On - state Current (A)



T<sub>J</sub> = 25 °C 1 0.5 1.0 1.5 2.0 2.5 3.0 Instantaneous On - state Voltage (V)

Fig. 7 - On-State Voltage Drop Characteristics



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Half Cycle Current Pulse (N)

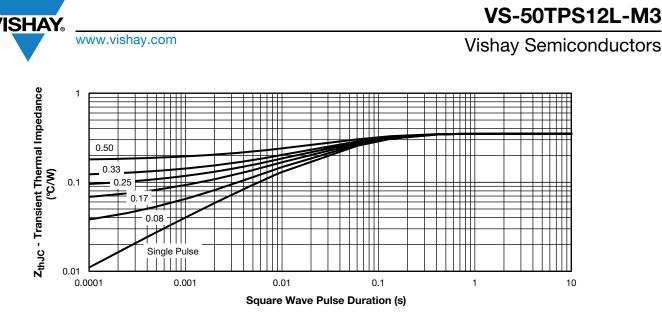


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

Device code	VS-	50	т	Р	S	12	L	-M3
	1	2	3	4	5	6	7	8
4  3  4  5	1 - 2 - 3 - 4 - 5 -	Cur Circ T = P = Typ S =	rent coo cuit conf thyristo TO-247 e of silio standar	'AD 3L p	50 A) n: backage ery recti	fier		0
	7 -	Pac	kage L	= long le gen-free	ead		ant, and	l termin

ORDERING INFORMATI	ON (example)		
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-50TPS12L-M3	25	contact factory	Antistatic plastic tubes

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95626
Part marking information	www.vishay.com/doc?95007

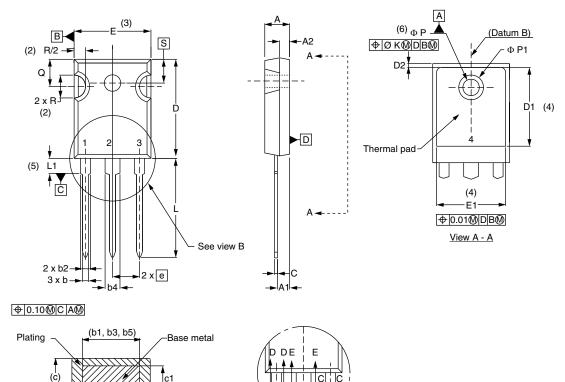
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## **TO-247AD 3L**

#### **DIMENSIONS** in millimeters and inches



(b, b2, b4) Section C - C, D - D, E - E

(4)

View B

	MILLIN	IETERS	INC	HES	NOTEO
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
e	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

<sup>(3)</sup> Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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